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## Silicon NPN Power Transistor

## 2SC3257

### DESCRIPTION

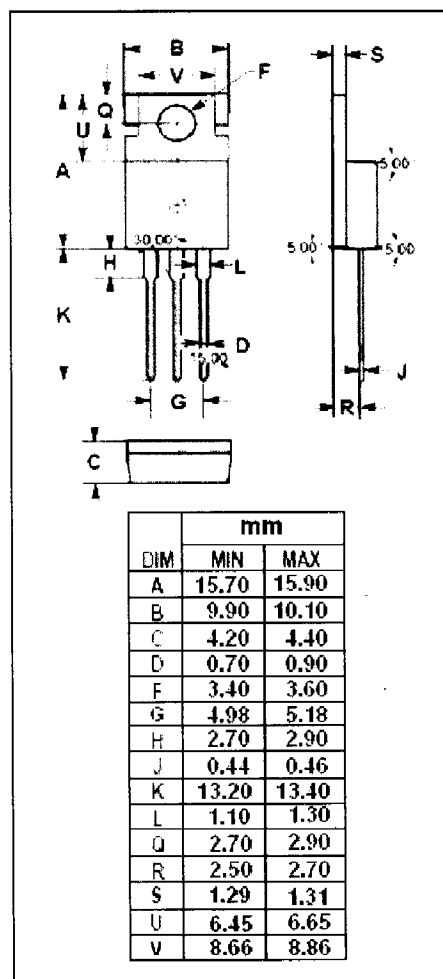
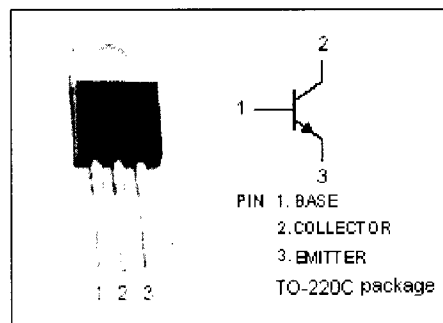
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 200V(\text{Min})$
- High Switching Speed

### APPLICATIONS

- Switching regulator and high voltage switching applications.
- High speed DC-DC converter applications.

### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	250	V
$V_{CEO}$	Collector-Emitter Voltage	200	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	10	A
$I_{CM}$	Collector Current-Peak	15	A
$I_B$	Base Current-Continuous	2	A
$P_C$	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.5	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	40	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

**Quality Semi-Conductors**

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## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	200			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	250			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=200\text{V}; I_E=0$			100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=7\text{V}; I_C=0$			1.0	mA
$h_{FE-1}$	DC Current Gain	$I_C=10\text{mA}; V_{CE}=5\text{V}$	15			
$h_{FE-2}$	DC Current Gain	$I_C=5\text{A}; V_{CE}=5\text{V}$	20		80	

## Switching times

$t_r$	Rise Time	$I_{B1}=-I_{B2}=0.6\text{A}; R_L=25\ \Omega;$ $V_{CC}\approx 150\text{V}$			1.0	$\mu\text{s}$
$t_{stg}$	Storage Time				2.5	$\mu\text{s}$
$t_f$	Fall Time				1.0	$\mu\text{s}$